

PUBLICATIONS

a) Papers published in peer-reviewed international journals

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- a.11. M. Pejović, J. Živković, Č. Milosavljević, **G. Ristić**, "Formative time determination in nitrogen-filled tube using statistical methods", *Japanese Journal of Applied Physics (Part 1)*, **34** (3), 1652-1656, 1995.
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b) Chapter in monograph

- b.1. M.S. Andjelković, **G.S. Ristić**, "Physical aspects of radiofrequency radiation dosimetry", In book: *Dosimetry in Bioelectromagnetics*, CRC Press, Taylor&Francis Group, 119-138, 2017.
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